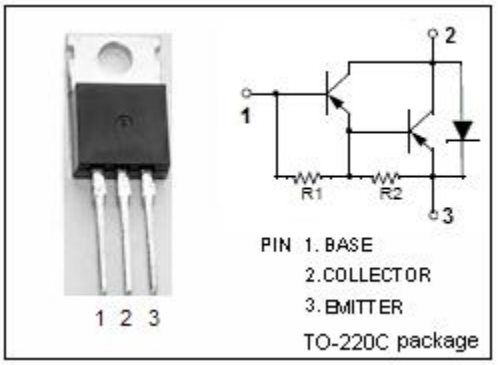
isc Silicon PNP Darlington Power Transistor 2SB955

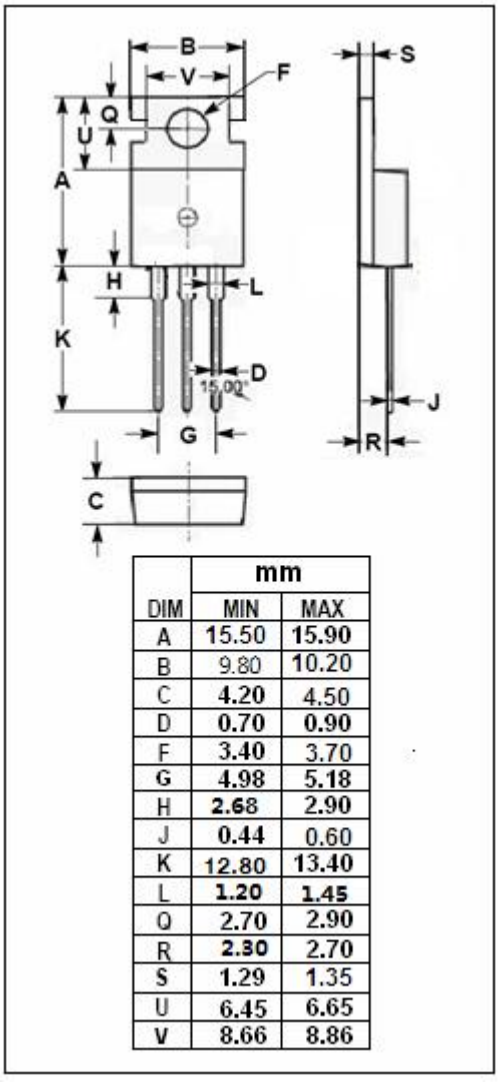
DESCRIPTION

- High DC Current Gain-
  : h_{FE} = 1000(Min)@ I_C= -5A
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$ = -120V(Min)
- Low Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$ = -1.5V(Max)@ I_C= -5A
- Complement to Type 2SD1126
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for power switching applications.



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-10	A
I_{CM}	Collector Current-Peak	-15	A
P_C	Collector Power Dissipation T_C=25℃	50	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -25mA, R_{BE}= ∞	-120			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -200mA, I_E= 0	-7			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= -5A, I_B= -10mA			-1.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= -10A, I_B= -0.1A			-3.0	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= -5A, I_B= -10mA			-2.0	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C= -10A, I_B= -0.1A			-3.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -120V, I_E= 0			-100	μA
I_{CEO}	Collector Cutoff Current	V_{CE}= -100V, R_{BE}= ∞			-10	μA
h_{FE}	DC Current Gain	I_C= -5A; V_{CE}= -3V	1000		20000	